Analog Power AM3902N

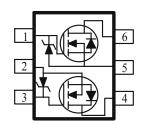
Dual N-Channel Logic Level MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	r _{DS(on)} (OHM)	$I_{D}(A)$			
25	$4.0 @ V_{GS} = 4.5 V$	0.4			
	$5.1 @ V_{GS} = 2.5V$	0.2			

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)							
Paramete r	Symbol	Maximum	Units				
Drain-Source Voltage			25	V			
Gate-Source Voltage			-8.5	V			
Continue Durin Compat ^a	$T_A=25^{\circ}C$		0.22				
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	П	0.17	A			
Pulsed Drain Current ^b		I_{DM}	0.5				
Continuous Source Current (Diode Conduction) ^a	I_S	±0.3	A				
D a	$T_A=25^{\circ}C$	D	0.9	W			
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	LD	0.7	VV			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum lunation to Ambient ^a	t <= 5 sec	D	140	°C/W		
Maximum Junction-to-Ambient ^a	Steady-State	R_{THJA}	180	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Crymbal	Test Conditions	Limits			Unit		
r ar ameter	Symbol	Test Conditions	Min	Тур	Max	1 Cint		
Switch Off Characteristics								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \text{ uA}$	25			V		
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	0.67	0.85	1.5	v		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = 8 V$			100	nA		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{SS} = 20 \text{ V}, V_{SS} = 0 \text{ V}, V_{SS} = 55^{\circ}\text{C}$			1 10	uA		
Switch On Characteristics		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	<u> </u>		10	<u> </u>		
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 2.5 \text{ V}$	0.2			Α		
		$V_{GS} = 2.5 \text{ V}, I_D = 0.2 \text{ A}$		3.8	5.0			
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 2.5 \text{ V}, I_D = 0.2 \text{ A T}_J = 55^{\circ}\text{C}$		4.0	5.5	Ω		
		$V_{GS} = 4.5 \text{ V}, I_D = 0.4 \text{ A}$		3.1	4.0	1		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 5 \text{ V}, I_D = 0.4 \text{ A}$		0.25		S		
Diode Forward Voltage	V_{SD}	$I_S = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.85	1.20	V		
Dynamic ^b	_							
Total Gate Charge	Q_{g}			0.5	0.71			
Gate-Source Charge	Q_{gs}	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 0.2 \text{ A}$		0.22		nC		
Gate-Drain Charge	Q_{gd}			0.07				
Input Capacitance	C_{iss}	V = 15 V V = 0 V		10				
Output Capacitance	C_{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		6		pF		
Reverse Transfer Capacitance	C_{rss}			2				
Switching								
Turn-On Delay Time	$t_{d(on)}$			5	10			
Rise Time	$t_{\rm r}$	$V_{DD} = 6 \text{ V}, \qquad I_D = 0.5 \text{ A},$		4.5	10	l nc		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_G = 50 \Omega$		4	8	ns		
Fall-Time	t_{f}			3.2	7			

Notes

- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics

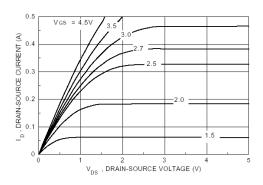


Figure 1. On-Region Characteristics

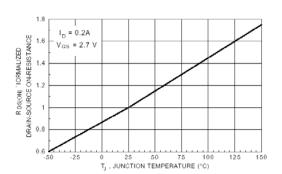


Figure 3. On-Resistance Variation with Temperature

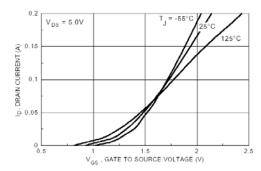


Figure 5. Transfer Characteristics

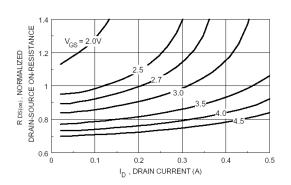


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

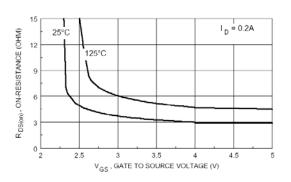


Figure 4. On-Resistance Variation with Gate to Source Voltage

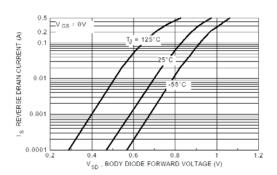
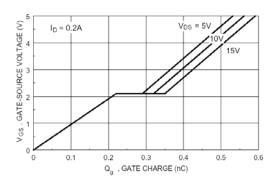


Figure 6. Body Diode Forward Voltage

Variation with Source Current and

Temperature

Typical Electrical Characteristics



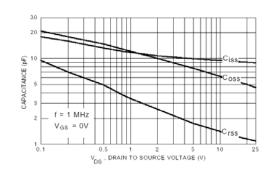
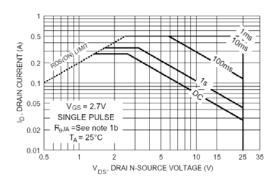


Figure 7. Gate Charge Characteristics

Figure 8. Capacitance Characteristics



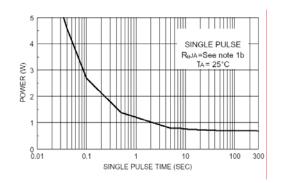


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power
Dissipation

Normalized Thermal Transient Junction to Ambient

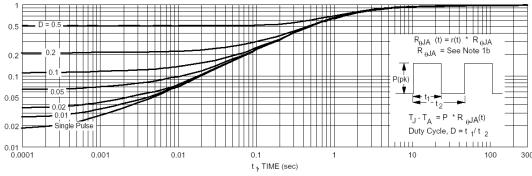
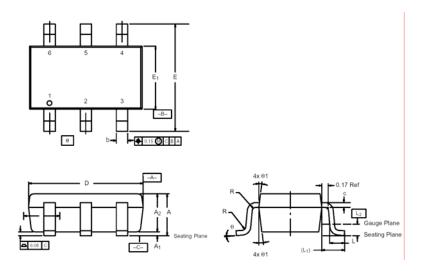


Figure 11. Transient Thermal Response Curve

Package Information

TSOP-6: 6LEAD



	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	_	0.043
A ₁	0.01	_	0.10	0.0004	_	0.004
A ₂	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	_	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	_	_	0.004	-	_
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		